

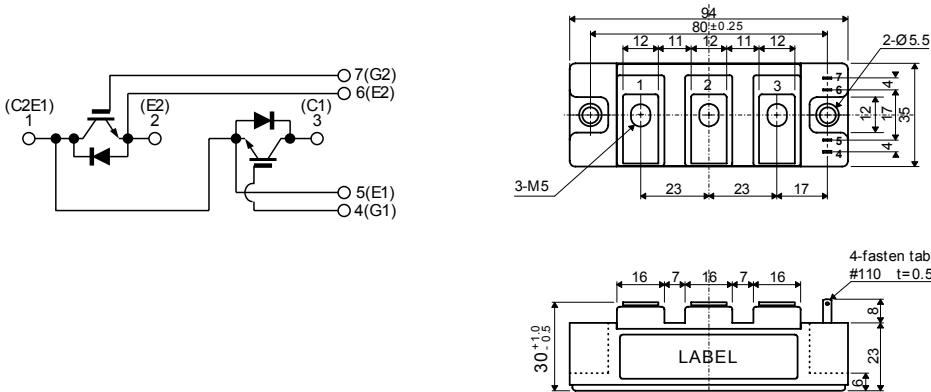
IGBT Module-Dual

100A, 600V

PDMB100E6

□ 回路図 : *CIRCUIT*

□ 外形寸法図 : *OUTLINE DRAWING*



Dimension: [mm]

□ 最大定格 : *MAXIMUM RATINGS* ($T_c = 25^\circ\text{C}$)

Item		Symbol	Rated Value	Unit
コレクタ・エミッタ間電圧 Collector-Emitter Voltage		V_{CES}	600	V
ゲート・エミッタ間電圧 Gate-Emitter Voltage		V_{GES}	± 20	V
コレクタ電流 Collector Current	DC	I_C	100	A
	1ms	I_{CP}	200	
コレクタ損失 Collector Power Dissipation		P_C	400	W
接合温度 Junction Temperature Range		T_j	$-40 \sim +150$	$^\circ\text{C}$
保存温度 Storage Temperature Range		T_{stg}	$-40 \sim +125$	$^\circ\text{C}$
絶縁耐圧(Terminal to Base AC, 1 minute) Isolation Voltage		V_{ISO}	2,500	V (RMS)
締め付けトルク Mounting Torque	Module Base to Heatsink	F_{tor}	2	N·m (kgf·cm)
	Busbar to Main Terminal		2 (20.4)	

□ 電気的特性 : *ELECTRICAL CHARACTERISTICS* ($T_c = 25^\circ\text{C}$)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
コレクタ遮断電流 Collector-Emitter Cut-Off Current		I_{CES}	$V_{CE} = 600\text{V}, V_{GE} = 0\text{V}$	—	—	1.0	mA
ゲート漏れ電流 Gate-Emitter Leakage Current		I_{GES}	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}$	—	—	1.0	μA
コレクタ・エミッタ間飽和電圧 Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 100\text{A}, V_{GE} = 15\text{V}$	—	2.1	2.6	V
ゲートしきい値電圧 Gate-Emitter Threshold Voltage		$V_{GE(th)}$	$V_{CE} = 5\text{V}, I_C = 100\text{mA}$	4.0	—	8.0	V
入力容量 Input Capacitance		C_{ies}	$V_{CE} = 10\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	—	5,000	—	pF
スイッチング時間 Switching Time	上昇時間 Rise Time	t_r	$V_{CC} = 300\text{V}$ $R_L = 3.0\Omega$ $R_G = 8.2\Omega$ $V_{GE} = \pm 15\text{V}$	—	0.15	0.30	μs
	ターンオン時間 Turn-on Time	t_{on}		—	0.25	0.40	
	下降時間 Fall Time	t_f		—	0.10	0.35	
	ターンオフ時間 Turn-off Time	t_{off}		—	0.35	0.70	

□ フリーホイーリングダイオードの特性 : *FREE WHEELING DIODE RATINGS & CHARACTERISTICS* ($T_c = 25^\circ\text{C}$)

I t e m		S y m b o l	R a t e d V a l u e		U n i t
順電流 Forward Current	DC	I_F	100		A
	1 m s	I_{FM}	200		

C h a r a c t e r i s t i c							S y m b o l	T e s t C o n d i t i o n	M i n .	T y p .	M a x .	U n i t
順電圧 Peak Forward Voltage		V_F	$I_F = 100A, V_{GE} = 0V$			—	1.9	2.4	V			
逆回復時間 Reverse Recovery Time		t_{rr}	$I_F = 100A, V_{GE} = -10V$ $di/dt = 200A/\mu s$			—	0.15	0.25	μs			

□ 熱的特性 : *THERMAL CHARACTERISTICS*

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
熱抵抗 Thermal Impedance	IGBT	$R_{th(j-c)}$	Junction to Case (T_c 測定点チップ直下)	—	—	0.31	$^\circ\text{C}/\text{W}$
	Diode			—	—	0.65	

PDMB100E6

Fig.1- Output Characteristics (Typical)

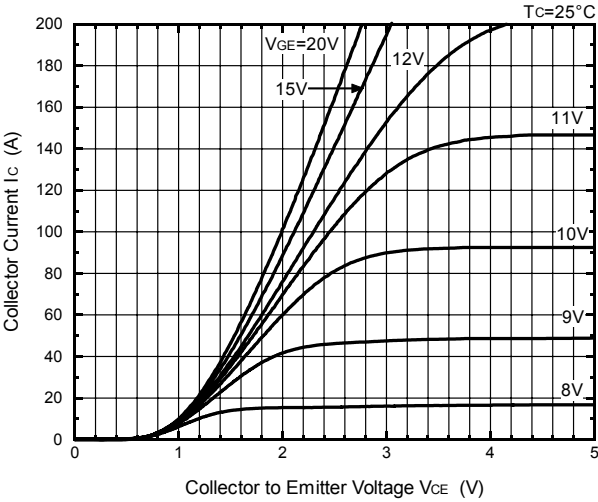


Fig.2- Output Characteristics (Typical)

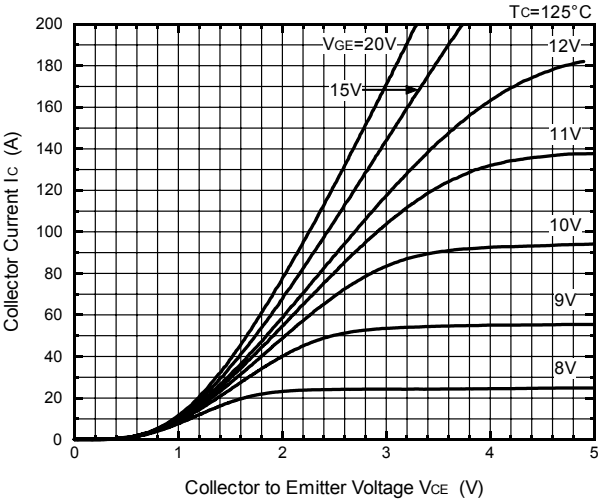


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

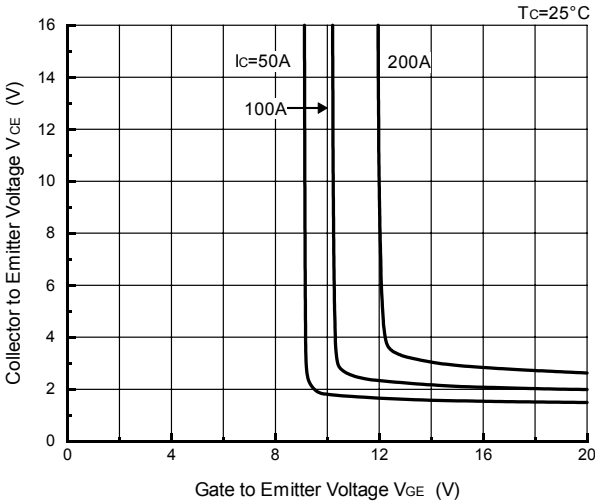


Fig.4- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

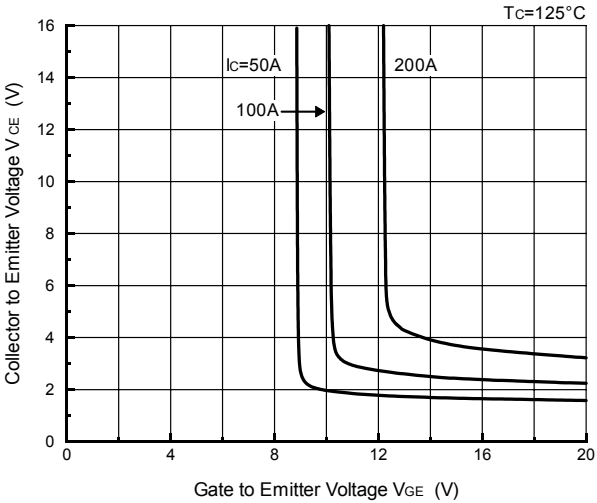


Fig.5- Gate Charge vs. Collector to Emitter Voltage (Typical)

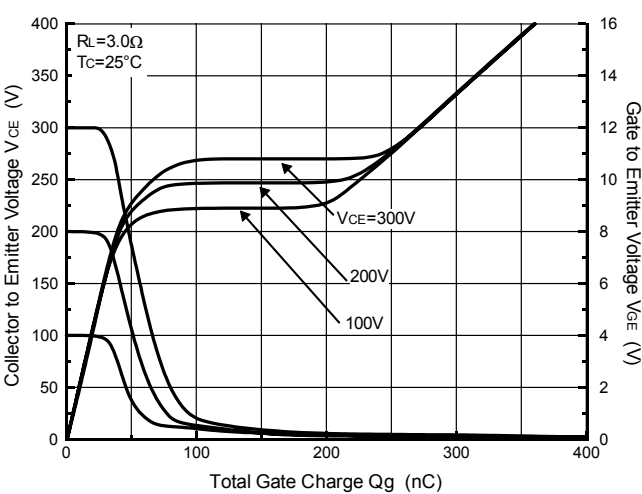
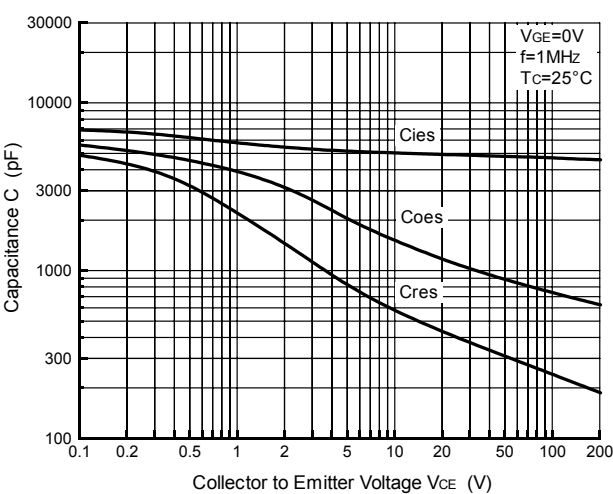


Fig.6- Capacitance vs. Collector to Emitter Voltage (Typical)



P D M B 1 0 0 E 6

Fig.7- Collector Current vs. Switching Time (Typical)

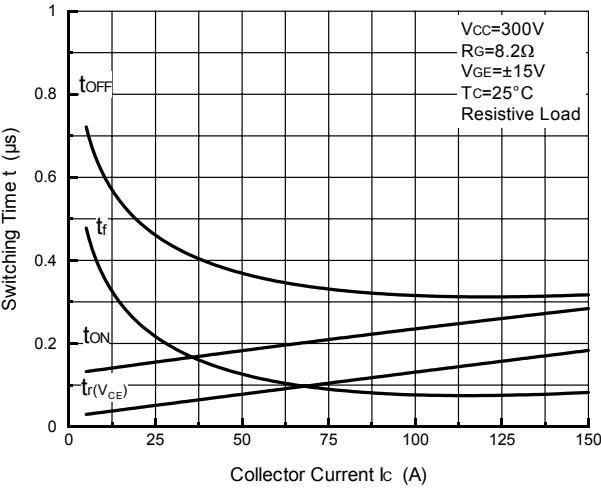


Fig.8- Series Gate Impedance vs. Switching Time (Typical)

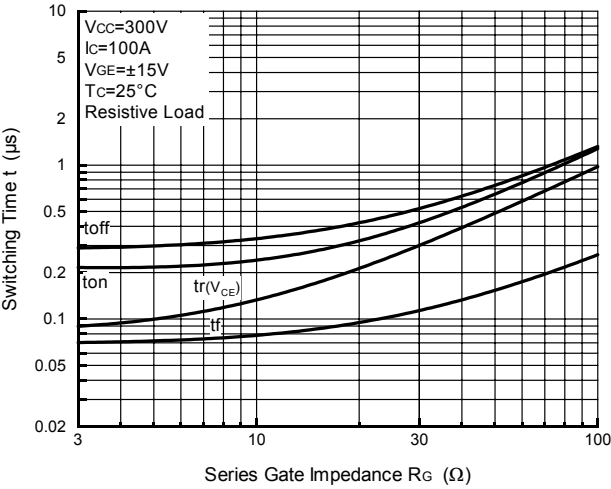


Fig.9- Collector Current vs. Switching Time

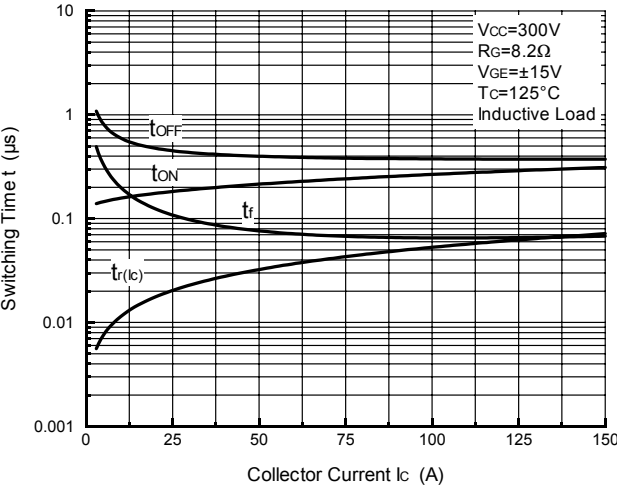


Fig.10- Series Gate Impedance vs. Switching Time

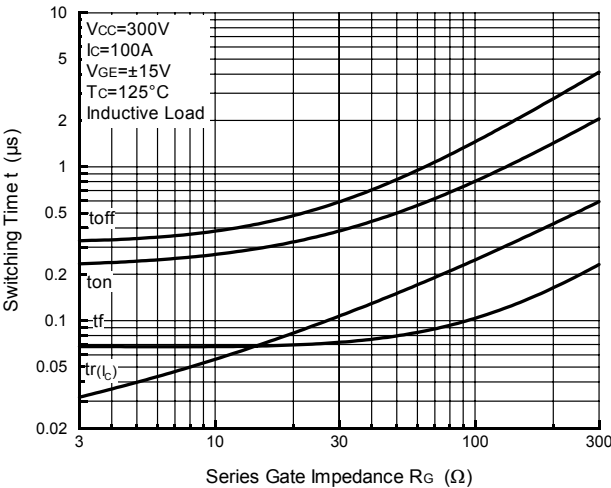


Fig.11- Collector Current vs. Switching Loss

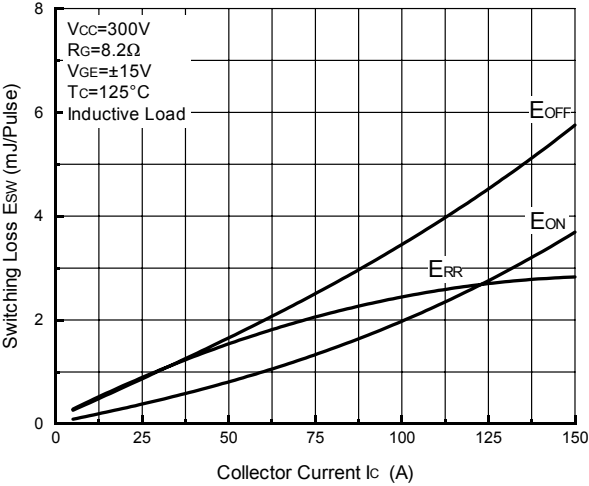
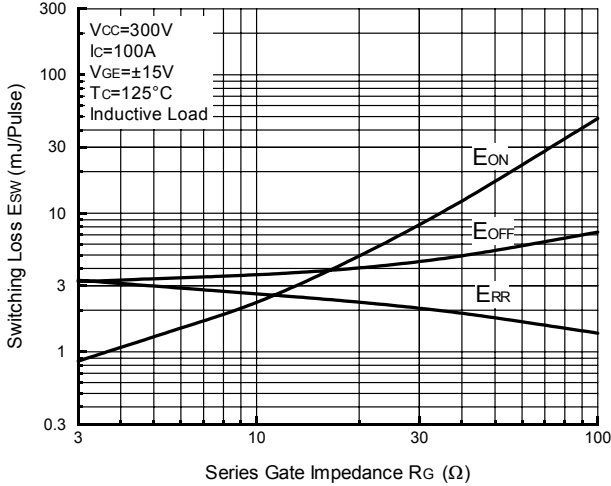


Fig.12- Series Gate Impedance vs. Switching Loss



P D M B 1 0 0 E 6

Fig.13- Forward Characteristics of Free Wheeling Diode (Typical)

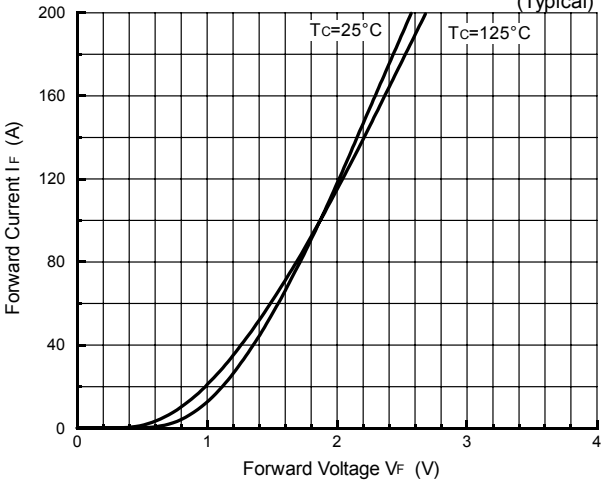


Fig.14- Reverse Recovery Characteristics (Typical)

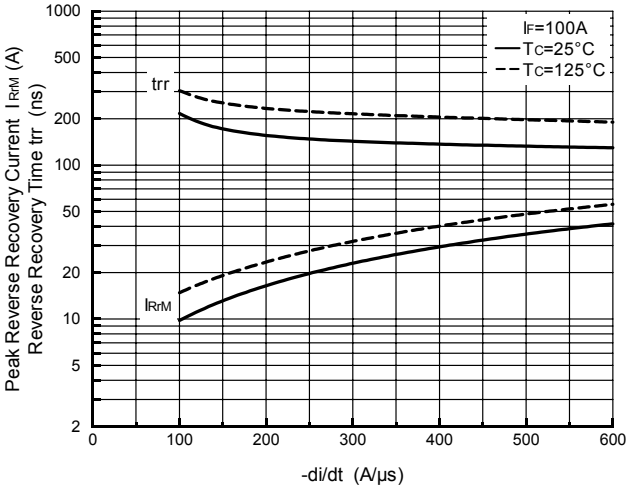


Fig.15- Reverse Bias Safe Operating Area

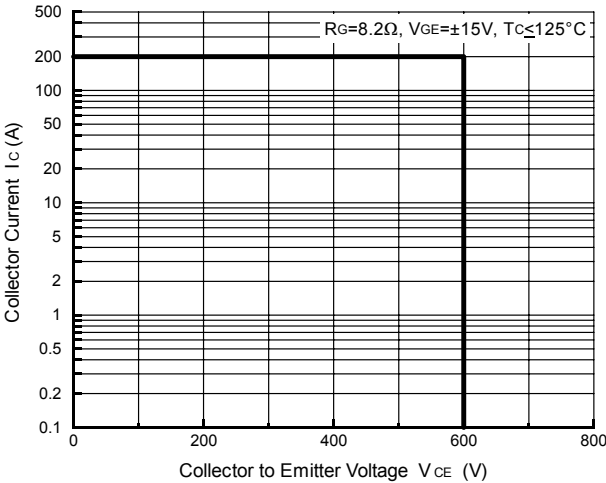


Fig.16- Transient Thermal Impedance

